

Silicon NPN Power Transistors

2SD772 2SD772A 2SD772B

DESCRIPTION

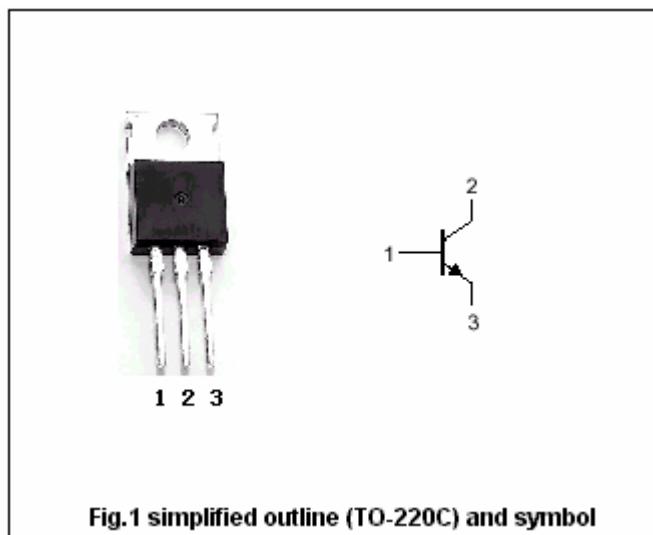
- With TO-220C package
- High breakdown voltage
- High speed switching

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD772	Open emitter	150	V
		2SD772A		200	
		2SD772B		250	
V_{CEO}	Collector-emitter voltage		Open base	80	V
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current (DC)			5	A
I_{CM}	Collector current-Peak			10	A
P_C	Collector dissipation		$T_C=25^\circ$	40	W
T_j	Junction temperature			150	$^\circ$
T_{stg}	Storage temperature			-50~150	$^\circ$

Silicon NPN Power Transistors**2SD772 2SD772A 2SD772B****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage		I _C =0.2A; L=25mH	80			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =5A; I _B =1A			1.6	V
V _{BE}	Base-emitter on voltage		I _C =5A; V _{CE} =4V			1.5	V
I _{CBO}	Collector cut-off current	2SD772	V _{CB} =150V; I _E =0			1.0	mA
		2SD772A	V _{CB} =200V; I _E =0				
		2SD772B	V _{CB} =250V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain		I _C =5A; V _{CE} =4V	14			
t _f	Fall time		I _C =5A; V _{EB} =-5V, I _{B1} =0.8A			1	μs
f _T	Transition frequency		I _C =0.5A; V _{CE} =10V		40		MHz

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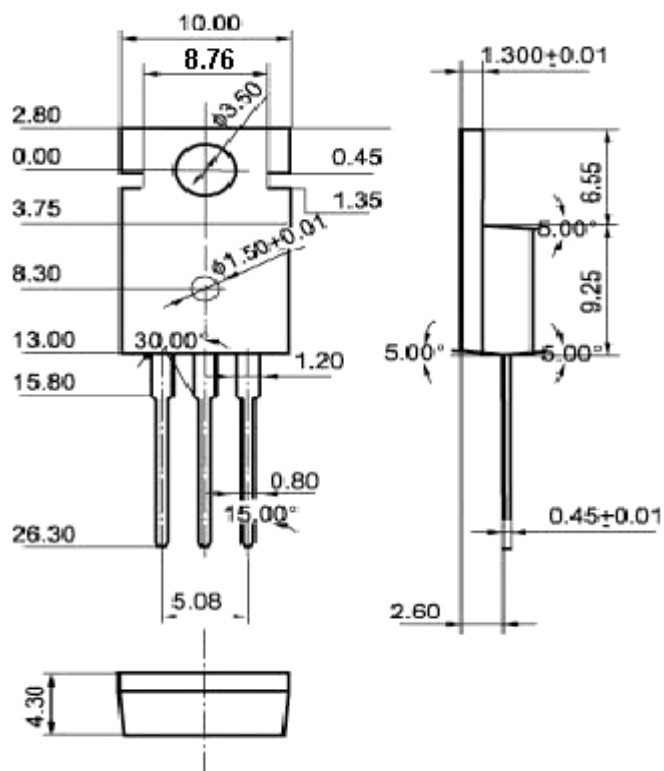


Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)